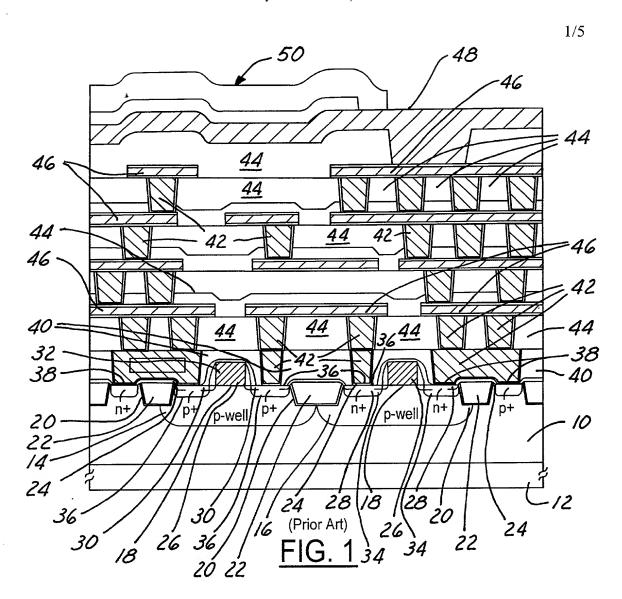
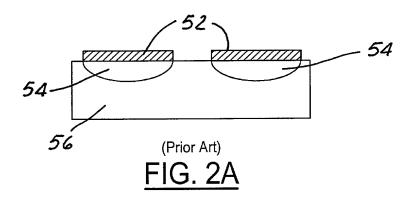
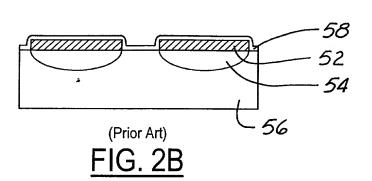
For: Method Of Wet Etching Low Dielectric Constant Materials
Attorney Docket No.: 67,200-473

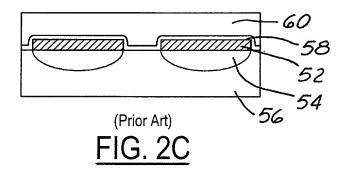




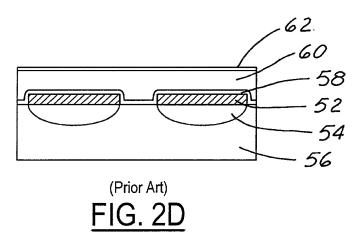
For: Method Of Wet Etching Low Dielectric Constant Materials

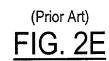
Attorney Docket No.: 67,200-473

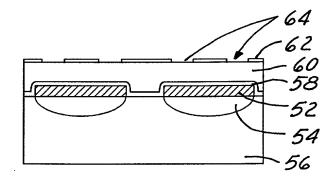




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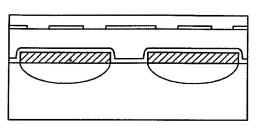






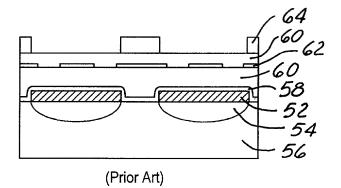
For: Method Of Wet Etching Low Dielectric Constant Materials

Attorney Docket No.: 67,200-473



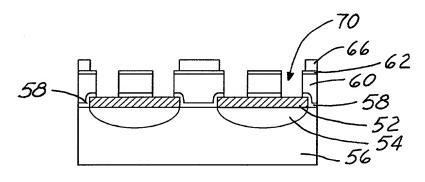
(Prior Art)

FIG. 2F



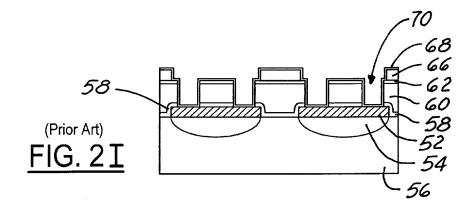
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FIG. 2G



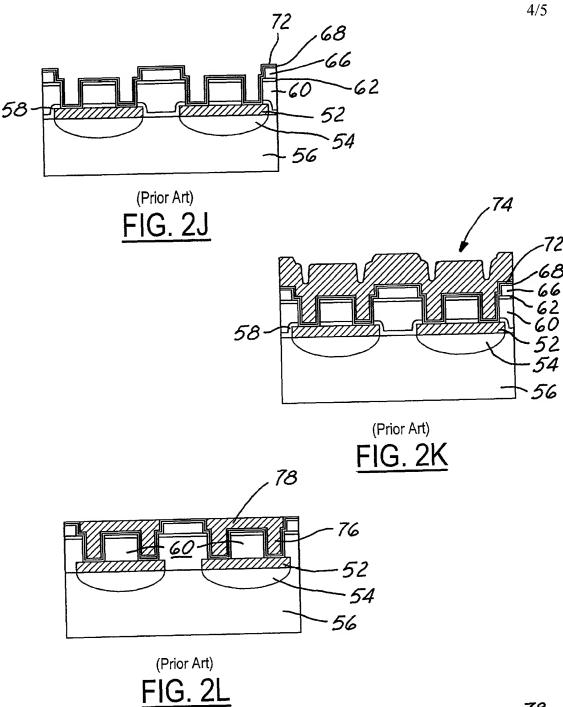
(Prior Art)

FIG. 2H



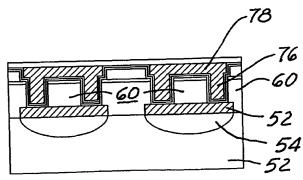
For: Method Of Wet Etching Low Dielectric Constant Materials

Attorney Docket No.: 67,200-473



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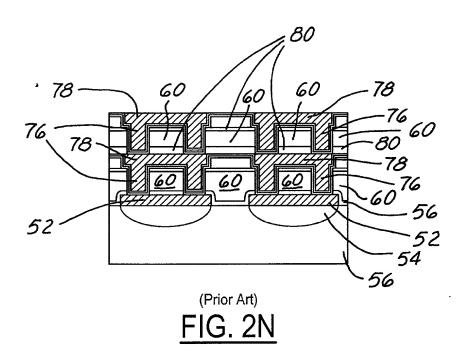
(Prior Art)
FIG. 2M



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Providing or Forming a Semiconductor Device having Two Metal Interconnects and a Low Dielectric Constant Material There Between

Etching the Low Dieletric Constant Material with an Aqueous Solution Including HF and HCL

Analyzing the Etched Device with a Scanning Electron Microscope

FIG. 3